## MAX222 5-V DUAL RS-232 LINE DRIVER/RECEIVER WITH ±15-kV ESD PROTECTION

SLLS590D - SEPTEMBER 2003 - REVISED AUGUST 2004

- ESD Protection for RS-232 Bus Pins
  ±15-kV Human-Body Model
- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operates at 5-V V<sub>CC</sub> Supply
- Operates Up To 200 kbit/s
- Low Supply Current in Shutdown Mode . . . 2 μA Typical
- External Capacitors . . . 4 × 0.1 μF
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Applications
  - Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment

#### DW OR N PACKAGE (TOP VIEW) NC [ 18 SHDN C1+ ∏ 2 17 VCC V+ **∏** 3 16 GND C1- $\Pi$ 4 15 DOUT1 С2+ Г 5 14 RIN1 C2-6 13 ROUT1 V- **1** 7 12**∏** DIN1 DOUT2 $\Pi$ 8 11 ∏ DIN2 RIN2 10 ROUT2

### description/ordering information

The MAX222 consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). This device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 5-V supply. This device operates at data signaling rates up to 200 kbit/s and a maximum of 30-V/μs driver output slew rate. By using SHDN, all receivers can be disabled.

#### ORDERING INFORMATION

TA	PACI	KAGET	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	PDIP (N)	Tube of 20	MAX222CN	MAX222CN
0°C to 70°C	0010 (5110	Tube of 20	MAX222CDW	MAYOOO
	SOIC (DW)	Reel of 1000	MAX222CDWR	MAX222C
	PDIP (N)	Tube of 20	MAX222IN	MAX222IN
-40°C to 85°C	SOIC (DW)	Tube of 20	MAX222IDW	MAX222I
	301C (DVV)	Reel of 1000	MAX222IDWR	IVIAAZZZI

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



#### **Function Tables**

### **EACH DRIVER**

INPUT DIN	OUTPUT DOUT
L	Н
Н	L

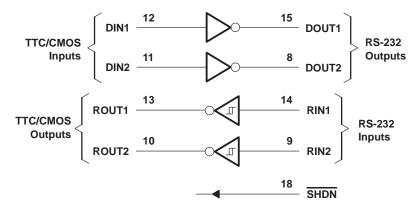
H = high level, L = low level

#### **EACH RECEIVER**

INPUT R <sub>IN</sub>	OUTPUT ROUT
L	Н
Н	L
Open	Н

H = high level, L = low level, Open = input disconnected or connected driver off

## logic diagram (positive logic)





## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage ra	nge, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Input voltage rang	ge, V <sub>I</sub> : Drivers	$\dots$ -0.3 V to V <sub>CC</sub> - 0.3 V
	Receivers	±30 V
Output voltage rai	nge, V <sub>O</sub> : Drivers	±15 V
	Receivers	$\dots$ -0.3 V to V <sub>CC</sub> + 0.3 V
Short-circuit durat	tion, D <sub>OUT</sub>	Continuous
Package thermal	impedance, θ <sub>JA</sub> (see Notes 2 and 3): DW package	ge TBD°C/W
	N package	TBD°C/W
Operating virtual j	junction temperature, T <sub>J</sub>	150°C
	ure range, T <sub>sta</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- 2. Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is P<sub>D</sub> = (T<sub>J</sub>(max) T<sub>A</sub>)/θ<sub>JA</sub>. Operating at the absolute maximum T<sub>J</sub> of 150°C can affect reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.

## recommended operating conditions (see Note 4 and Figure 4)

		MIN	NOM	MAX	UNIT
VCC	Supply voltage	4.5	5	5.5	V
.,	Driver high-level input voltage DIN	2			V
VIH	Shutdown high-level input voltage SHDN	2			V
,,	Driver low-level input voltage DIN			0.8	V
VIL	Shutdown low-level input voltage SHDN			8.0	V
.,	Driver input voltage D <sub>IN</sub>	0		5.5	.,
VI	Receiver input voltage	-30		30	V
т.	MAX222C	0		70	°C
TA	Operating free-air temperature MAX222I	-40		85	-0

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
lee Committee comment		., 5.,	No load			4	10	4
Icc	Supply current	$V_{CC} = 5 V$	SHDN = V <sub>CC</sub>	$3~k\Omega$ on both inputs		15		mA
	Shutdown supply current					2	50	μΑ
SHDN	Shutdown input leakage current						±1	μΑ

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.



NOTES: 1. All voltages are with respect to network GND.

#### **DRIVER SECTION**

## electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDITIONS			TYP†	MAX	UNIT
Vон	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	$D_{IN} = GND$	5	8		V
VOL	Low-level output voltage	DOUT at R <sub>L</sub> = $3 \text{ k}\Omega$ to GND,	DIN = VCC	-5	-8		V
	Driver high-level input current	DIN = V <sub>CC</sub>			5	40	^
ΙΗ	Control high-level input current	SHDN = V <sub>CC</sub>			0.01	1	μΑ
	Driver low-level input current	DIN = 0 V			-5	-40	
IIL	Control low-level input current	SHDN = 0 V			-0.01	-1	μΑ
los‡	Short-circuit output current	V <sub>CC</sub> = 5.5 V,	VO = 0 V	±7	±22		mA
l <sub>off</sub>	Output leakage current	$V_{CC} = 5.5 \text{ V}, \overline{SHDN} = GND,$	V <sub>O</sub> = ±10 V		±0.01	±10	μΑ
r <sub>o</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	V <sub>O</sub> = ±2 V	300	10 M	·	Ω

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 5$  V, and  $T_A = 25$ °C.

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

## switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CO	ONDITIONS	MIN TYPT MAX		UNIT	
	Data rate	C <sub>L</sub> = 1000 pF, One D <sub>OUT</sub> switching,	$R_L = 3 \text{ k}\Omega$ , See Figure 1	200			kbit/s
<sup>t</sup> PLH (D)	Propagation delay time, low- to high-level output	See Figure 1			1.5	3.5	μs
<sup>t</sup> PHL (D)	Propagation delay time, high- to low-level output	See Figure 1			1.3	3.5	μs
tPHL (D) - tPLH (D)	Driver (+ to –) propagation delay difference				300		ns
t <sub>sk(p)</sub>	Pulse skew§	C <sub>L</sub> = 150 pF to 2500 pF	$R_L = 3 kΩ$ to 7 kΩ, See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	$R_L$ = 3 kΩ to 7 kΩ, $V_{CC}$ = 5 V	C <sub>L</sub> = 50 pF to 2500 pF	6	12	30	V/μs
tET	Driver output enable time (after SHDN goes high)				250		μs
<sup>t</sup> DT	Driver <u>output</u> disable time (after SHDN goes low)				300		ns

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.



<sup>\$</sup> Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

<sup>§</sup> Pulse skew is defined as |tplH - tpHL| of each channel of the same device.

#### **RECEIVER SECTION**

## electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
Vон	High-level output voltage	I <sub>OH</sub> = −1 mA	3.5	V <sub>CC</sub> – 0.2 V		V
VOL	Low-level output voltage	I <sub>OL</sub> = 3.2 mA			0.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.7	2.4	V
VIT-	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.8	1.3		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )		0.2	0.5	1	V
rį	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

### switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 3)

	PARAMETER	TEST CONDITIONS	MIN	түр†	MAX	UNIT
<sup>t</sup> PLH (R)	Propagation delay time, low- to high-level output	C <sub>L</sub> = 150 pF		0.6	1	μs
tPHL (R)	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF		0.5	1	μs
tPHL (R) - tPLH (R)	Receiver (+ to -) propagation delay difference			100		ns
tsk(p)	Pulse skew <sup>‡</sup>			100		ns

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC}$  = 5 V and  $T_A$  = 25°C.

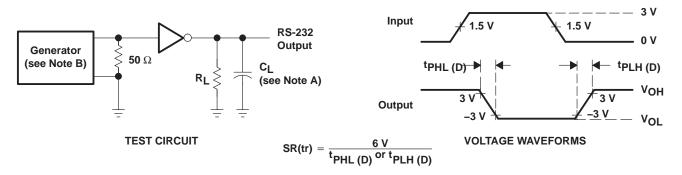
#### **ESD** protection

PIN	TEST CONDITIONS	TYP	UNIT
D <sub>OUT</sub> , R <sub>IN</sub>	Human-Body Model	±15	kV



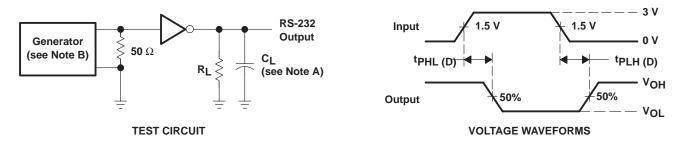
<sup>‡</sup> Pulse skew is defined as  $|t_{PLH} - t_{PHL}|$  of each channel of the same device. NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F, at  $V_{CC}$  = 5  $V \pm 0.5$  V.

#### PARAMETER MEASUREMENT INFORMATION



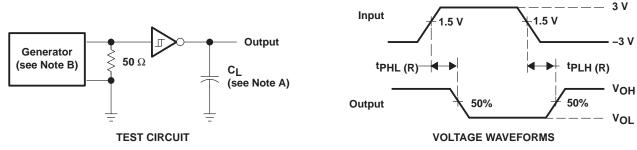
- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \ \Omega$ , 50% duty cycle,  $t_\Gamma \le 10 \ ns$ .

Figure 1. Driver Slew Rate



- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.

Figure 2. Driver Pulse Skew

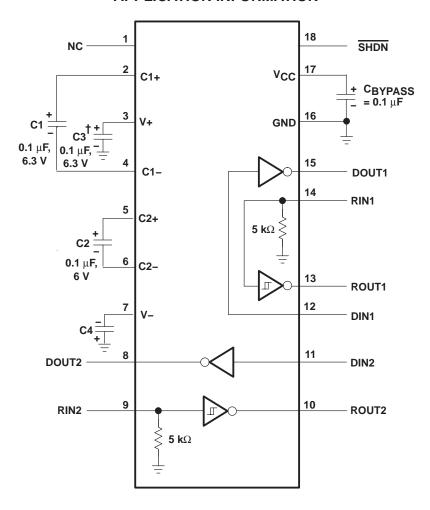


- NOTES: A. CL includes probe and jig capacitance.
  - B. The pulse generator has the following characteristics:  $Z_O$  = 50  $\Omega$ , 50% duty cycle,  $t_f \le 10$  ns,  $t_f \le 10$  ns.

Figure 3. Receiver Propagation Delay Times



## **APPLICATION INFORMATION**



†C3 can be connected to VCC or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Figure 4. Typical Operating Circuit and Capacitor Values

#### APPLICATION INFORMATION

## capacitor selection

The capacitor type used for C1–C4 is not critical for proper operation. The MAX222 requires 0.1- $\mu$ F capacitors, although capacitors up to 10  $\mu$ F can be used without harm. Ceramic dielectrics are suggested for the 0.1- $\mu$ F capacitors. When using the minimum recommended capacitor values, ensure that the capacitance value does not degrade excessively as the operating temperature varies. If in doubt, use capacitors with a larger (e.g., 2×) nominal value. The capacitors' effective series resistance (ESR), which usually rises at low temperatures, influences the amount of ripple on V<sub>+</sub> and V<sub>-</sub>.

Use larger capacitors (up to 10 μF) to reduce the output impedance at V<sub>+</sub> and V<sub>-</sub>.

Bypass  $V_{CC}$  to ground with at least 0.1  $\mu$ F. In applications sensitive to power-supply noise generated by the charge pumps, decouple  $V_{CC}$  to ground with a capacitor the same size as (or larger than) the charge-pump capacitors (C1–C4).

#### **ESD** protection

TI MAX222 devices have standard ESD protection structures incorporated on the pins to protect against electrostatic discharges encountered during assembly and handling. In addition, the RS232 bus pins (driver outputs and receiver inputs) of these devices have an extra level of ESD protection. Advanced ESD structures were designed to successfully protect these bus pins against ESD discharge of ±15-kV when powered down.

#### **ESD** test conditions

ESD testing stringently is performed by TI, based on various conditions and procedures. Contact TI for a reliability report that documents test setup, methodology, and results.

## **Human-Body Model**

The Human-Body Model (HBM) of ESD testing is shown in Figure 5, while Figure 6 shows the current waveform that is generated during a discharge into a low impedance. The model consists of a 100-pF capacitor, charged to the ESD voltage of concern, and subsequently discharged into the DUT through a 1.5-k $\Omega$  resistor.

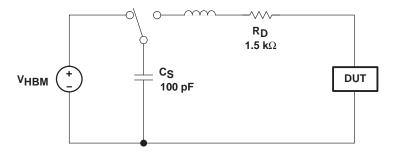


Figure 5. HBM ESD Test Circuit



#### **APPLICATION INFORMATION**

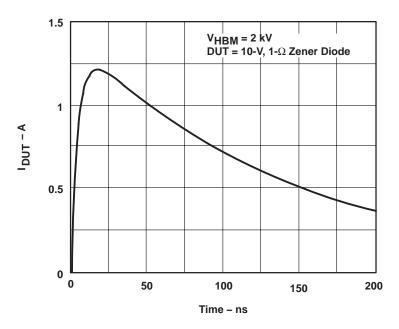


Figure 6. Typical HBM Current Waveform

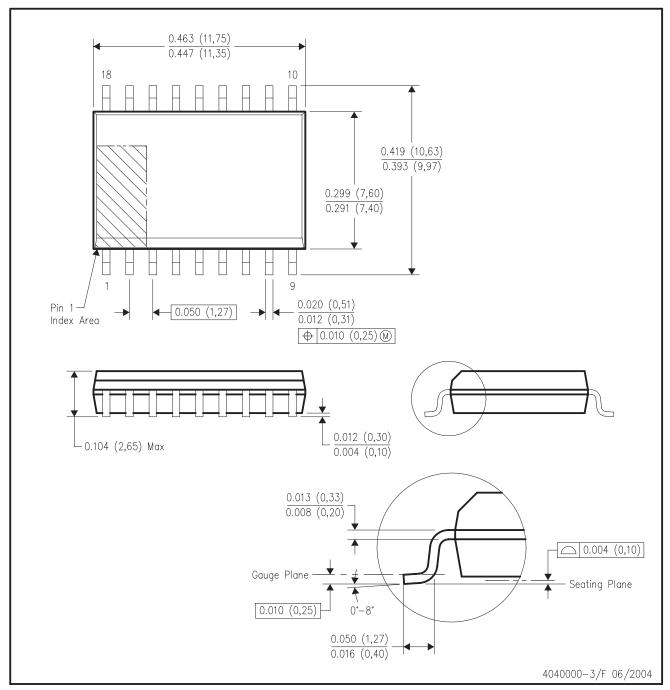
#### **Machine Model**

The Machine Model (MM) ESD test applies to all pins using a 200-pF capacitor with no discharge resistance. The purpose of the MM test is to simulate possible ESD conditions that can occur during the handling and assembly processes of manufacturing. In this case, ESD protection is required for all pins, not just RS-232 pins. However, after PC board assembly, the MM test no longer is as pertinent to the RS-232 pins.



## DW (R-PDSO-G18)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AB.



#### PACKAGE OPTION ADDENDUM



i.com 6-Dec-2006

#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
MAX222CDW	ACTIVE	SOIC	DW	18	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222CDWG4	ACTIVE	SOIC	DW	18	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222CDWR	ACTIVE	SOIC	DW	18	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222CDWRG4	ACTIVE	SOIC	DW	18	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222CN	ACTIVE	PDIP	N	18	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
MAX222CNE4	ACTIVE	PDIP	N	18	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
MAX222IDW	ACTIVE	SOIC	DW	18	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222IDWG4	ACTIVE	SOIC	DW	18	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222IDWR	ACTIVE	SOIC	DW	18	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222IDWRG4	ACTIVE	SOIC	DW	18	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
MAX222IN	ACTIVE	PDIP	N	18	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
MAX222INE4	ACTIVE	PDIP	N	18	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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## **PACKAGE OPTION ADDENDUM**

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## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



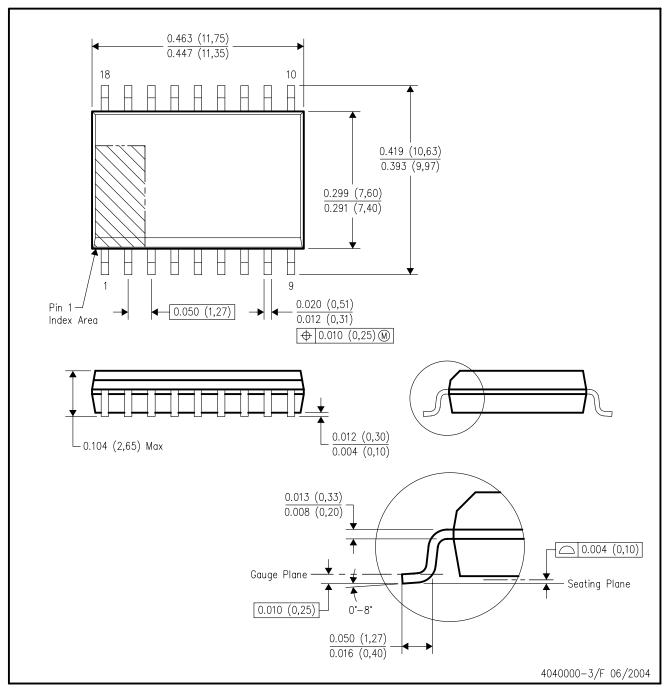
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



## DW (R-PDSO-G18)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AB.



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